

REMARKS

Claims 6-12, 14-16, 18, 20, 21, and 23-79 are pending, with claims 6, 9, 24, 31, 40, 48, 55, and 64 being independent and being amended by virtue of this response. Claims 1-5, 13, 17, 19, and 22 were previously cancelled without prejudice or disclaimer. No new matter is added.

Claims 6-12, 14-16, 18, 20, 21, and 23-71 are rejected under 35 U.S.C. 102(e) as being anticipated by U.S. Patent No. 5,922,125 to Zhang (Zhang). In response, Applicant respectfully submits that Zhang does not disclose or properly suggest all of the features of independent claims 6, 9, 24, 31, 40, 48, 55, and 64, as amended.

For example, independent claim 6, as amended, recites, “crystallizing the amorphous semiconductor film from the first metal element added region and the second metal element added region *in parallel to the substrate* to form a first crystalline portion and a second crystalline portion, respectively, in a crystalline semiconductor film.”

With respect to this claim element, the Office Action asserts at page 3 that Zhang discloses “crystallizing the amorphous semiconductor film (103) from the first metal element added region (101 and 102) and the second metal element added region (108 and 110) to form a first crystalline portion and a second crystalline portion, respectively, in a crystalline semiconductor film (see fig. 1A and 1B)...”

However, even assuming for the sake of response that this assertion is correct, Applicant submits that Zhang does not disclose or properly suggest, “crystallizing the amorphous semiconductor film from the first metal element added region and the second metal element added region *in parallel to the substrate*,” as recited in independent claim 6. Rather, Zhang explicitly states in, for example, column 4, lines 49-52, that “only vertical growth is carried out in the regions denoted by 108 to 110...” Thus, as illustrated in FIGS. 1b and 2 of Zhang, the regions 101/102/108/110 do not illustrate “crystallizing the amorphous semiconductor film from the first metal element added region and the second metal element added region *in parallel to the substrate*,” as recited in independent claim 6, nor does Zhang properly suggest such a claim feature(s), since Zhang states in the above-cited section that “horizontal growth does not take place when the region which nickel is held in contact with is small,” and, continuing in column

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4, lines 53-61, that such vertical growth regions are used as "stopper" regions for regions 104-107.

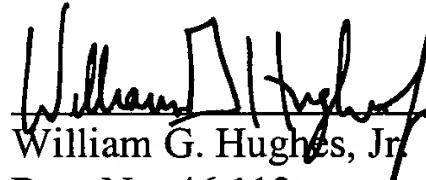
Accordingly, Applicant respectfully submits that independent claim 6 is in condition for allowance for at least the above reasons. Independent claims 9, 24, 31, 40, 48, 55, and 64, which recites a similar combination of features, are therefore also believed to be in condition for allowance for at least the same reasons. As a result, dependent claims 7, 8, 10-12, 14-16, 18, 20, 21, 23, 25-30, 32-39, 41-47, 49-54, 56-63, and 65-79 are believed to be in condition for allowance for at least the same reasons.

Based on the above, all claims are believed to be in condition for allowance, and such action is hereby requested in the Examiner's next official communication.

Please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

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